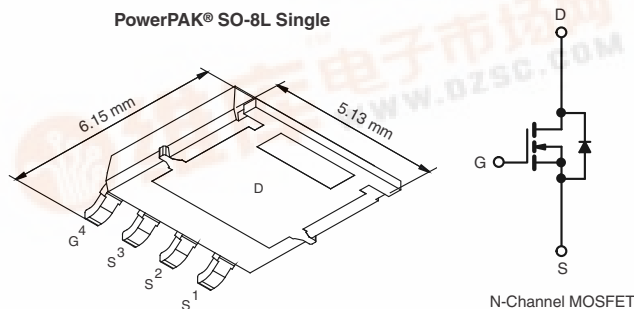


## Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	30
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.0039
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V	0.0042
I <sub>D</sub> (A)	32
Configuration	Single



### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>
- Find out more about Vishay's Automotive Grade Product Requirements at: [www.vishay.com/applications](http://www.vishay.com/applications)

AUTOMOTIVE  
 GRADE



RoHS  
 COMPLIANT  
 HALOGEN  
 FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ410EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current <sup>a</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	32
		T <sub>C</sub> = 125 °C	32
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	32	A
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	128	
Single Pulse Avalanche Current	I <sub>AS</sub>	58	
Single Pulse Avalanche Energy	E <sub>AS</sub>	168	mJ
Maximum Power Dissipation <sup>b</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	83
		T <sub>C</sub> = 125 °C	27
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R <sub>thJA</sub>	65	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.8	

### Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.
- See Solder Profile ([www.vishay.com/ppg?773257](http://www.vishay.com/ppg?773257)). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



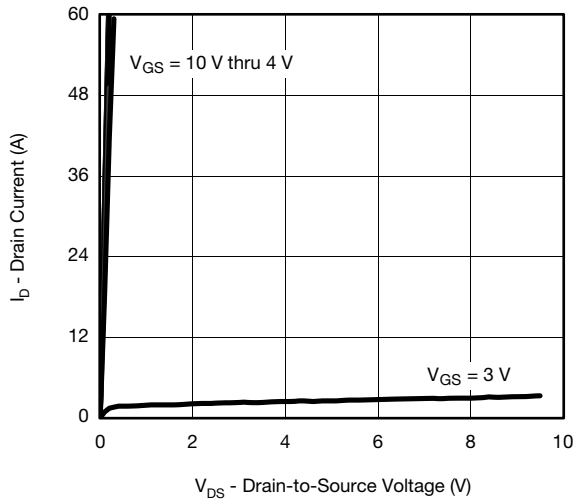
SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 30 V	-	-	1	μA
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> ≥ 5 V	30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.3 A	-	0.0030	0.0039	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.3 A, T <sub>J</sub> = 125 °C	-	0.0045	0.0060	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.3 A, T <sub>J</sub> = 175 °C	-	0.0055	0.0070	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8.7 A	-	0.0035	0.0042	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 16 A	-	93	-	S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz	-	4965	6210	pF
Output Capacitance	C <sub>oss</sub>		-	806	1010	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	325	410	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	-	73.5	110	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	12.8	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	8.2	-	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> = 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	15	23	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	11	17	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	40	60	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	9	14	
<b>Source-Drain Diode Ratings and Characteristics<sup>b</sup></b>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>		-	-	128	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.75	1.2	V

**Notes**

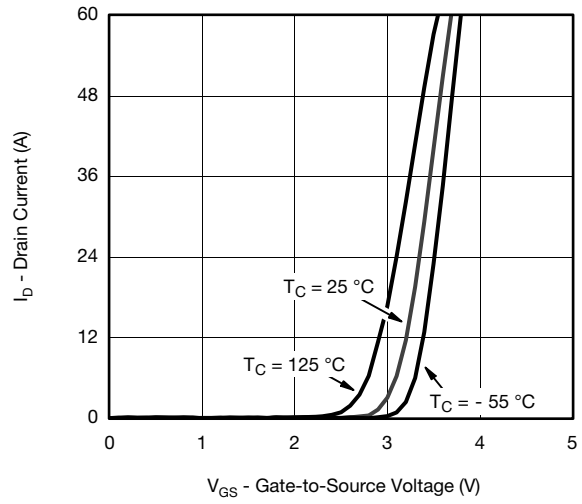
- g. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- h. Guaranteed by design, not subject to production testing.
- i. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

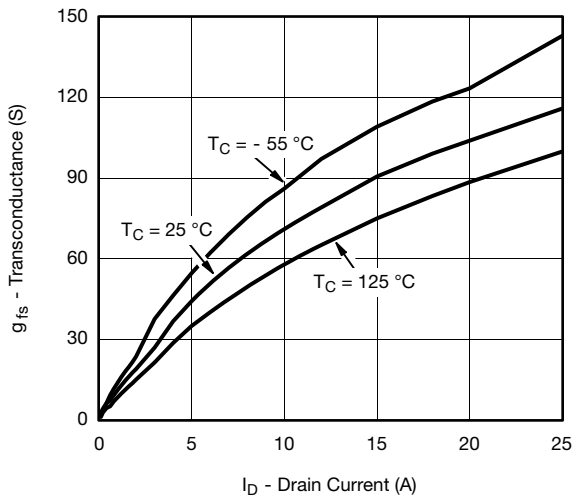
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



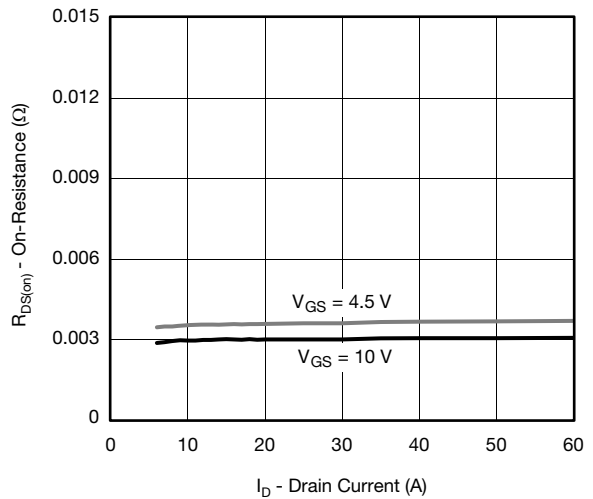
**Output Characteristics**



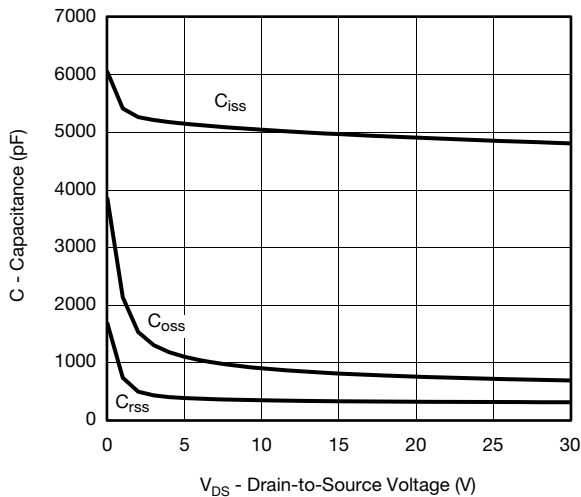
**Transfer Characteristics**



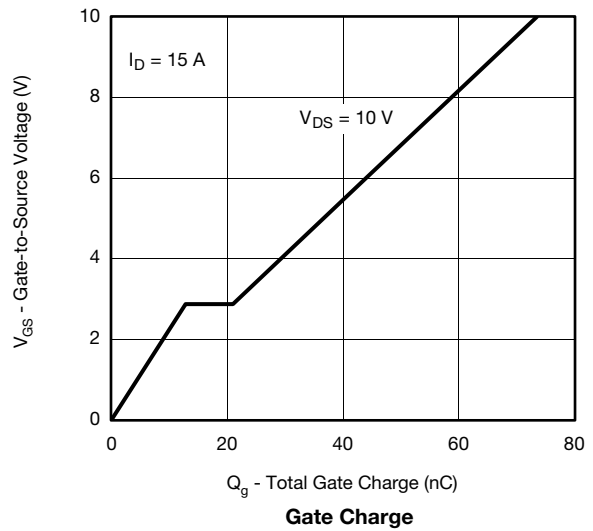
**Transconductance**



**On-Resistance vs. Drain Current**

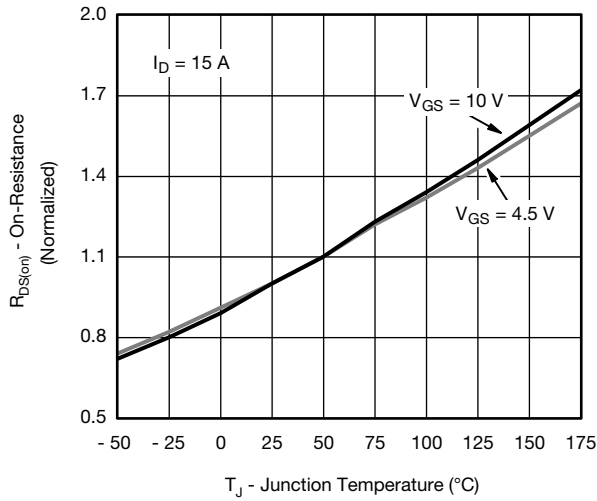


**Capacitance**

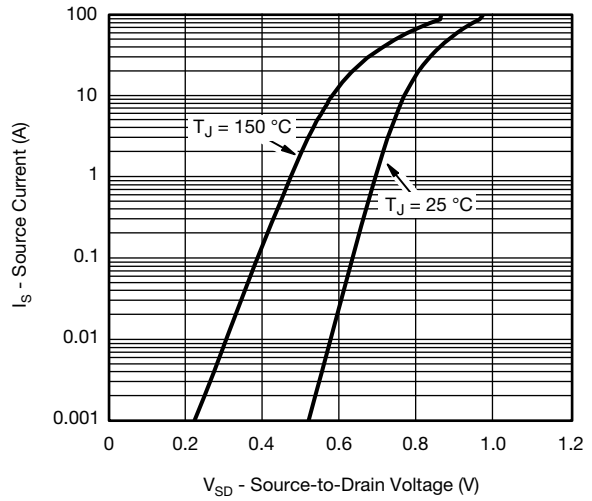


**Gate Charge**

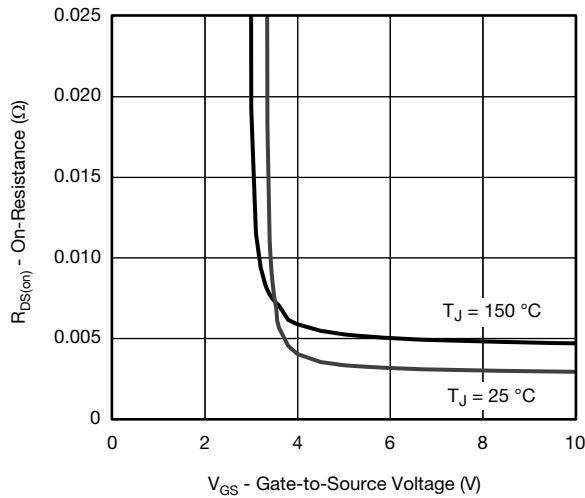
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



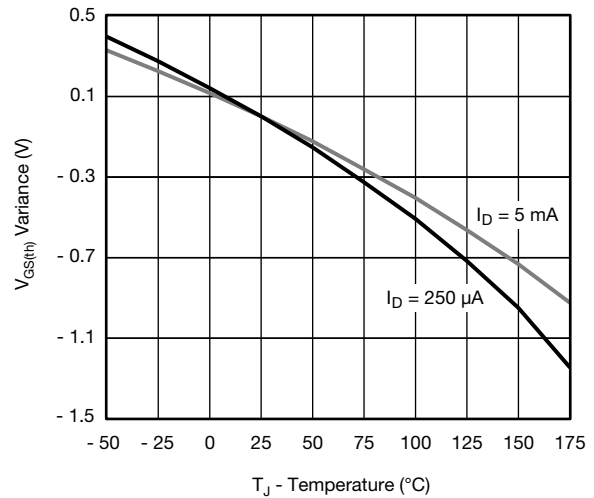
**On-Resistance vs. Junction Temperature**



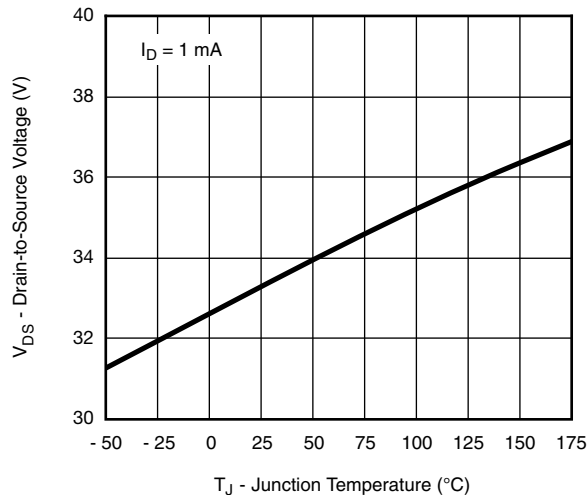
**Source Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

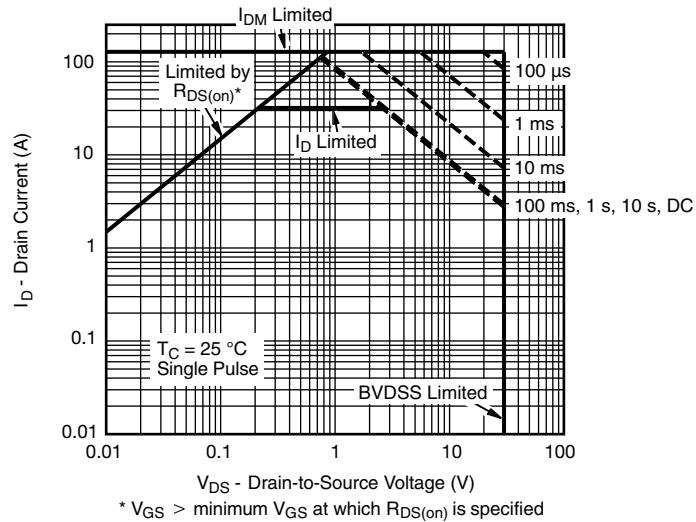


**Threshold Voltage**

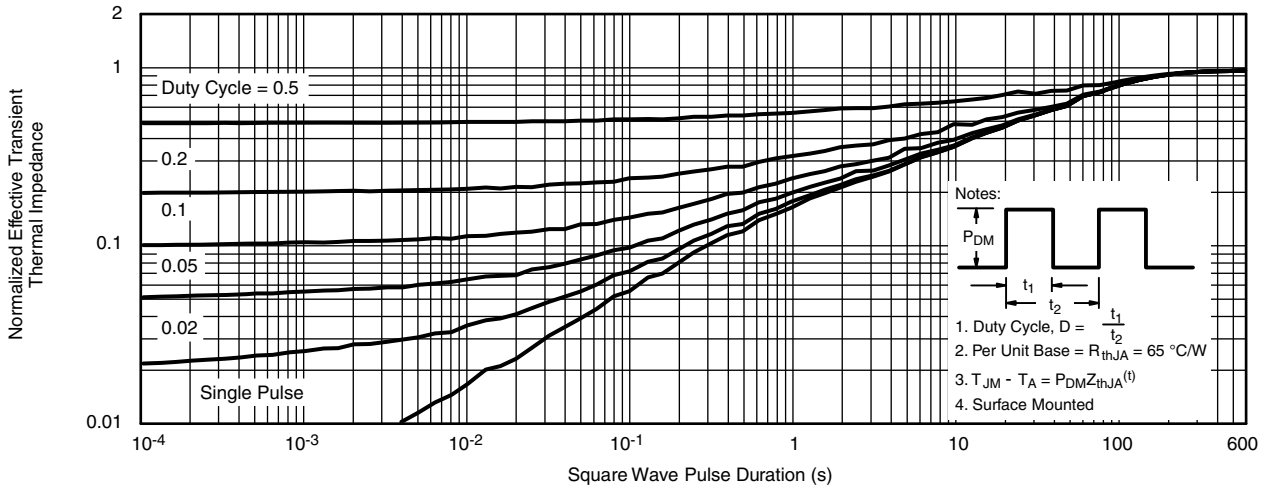


**Drain Source Breakdown vs. Junction Temperature**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

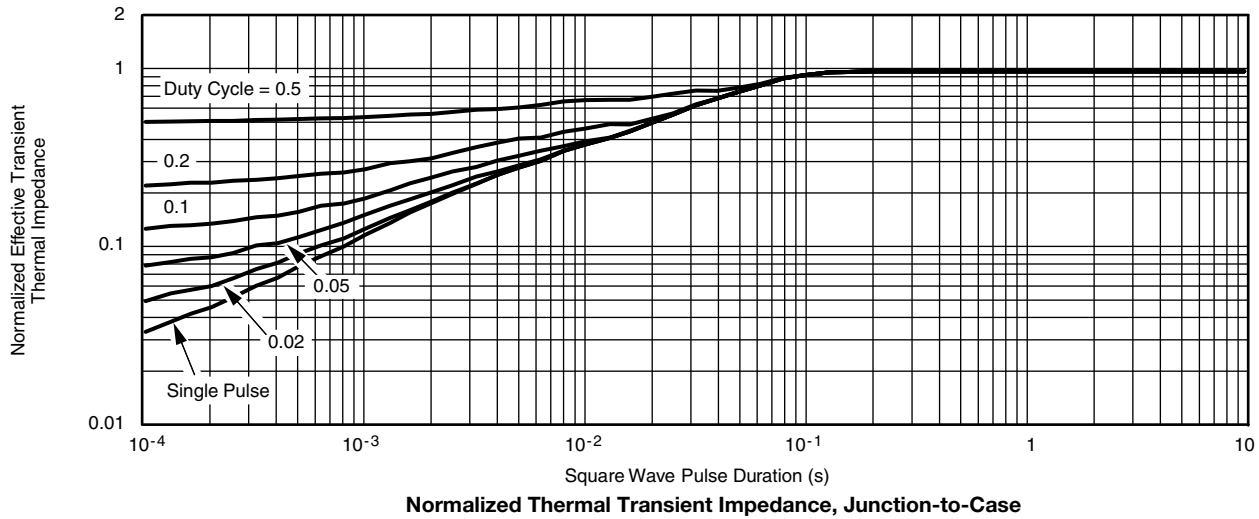


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

## THERMAL RATINGS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



### Note

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ )
    - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^\circ\text{C}$ )
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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